

NVMS011N04C

MOSFET – Power, Single N-Channel 40 V, 12 mΩ, 35 A

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- LFPAK4 Package, Industry Standard
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	40	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3)	I_D	35	A
		20	
Power Dissipation $R_{\theta JC}$ (Notes 1, 2)	P_D	28	W
		9.1	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)	I_D	13	A
		9.1	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)	P_D	3.8	W
		1.9	
Pulsed Drain Current	I_{DM}	173	A
Operating Junction and Storage Temperature	T_J, T_{stg}	-55 to + 175	°C
Source Current (Body Diode)	I_S	24	A
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}$, $I_{L(pk)} = 1.9$ A)	E_{AS}	75	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State	$R_{\theta JC}$	5.3	°C/W
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	39	

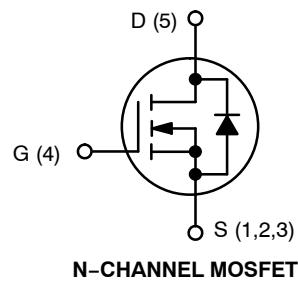
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.



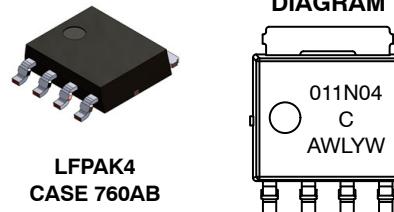
ON Semiconductor®

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$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	12 mΩ @ 10 V	35 A



N-CHANNEL MOSFET



LFPAK4
CASE 760AB

011N04 = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
W = Work Week

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

NVMYS011N04C

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(\text{BR})\text{DSS}}/T_J$				25		$\text{mV}/^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{GS}} = 0 \text{ V}, V_{\text{DS}} = 40 \text{ V}$	$T_J = 25^\circ\text{C}$		10		μA
			$T_J = 125^\circ\text{C}$			250	
Gate-to-Source Leakage Current	I_{GSS}	$V_{\text{DS}} = 0 \text{ V}, V_{\text{GS}} = 20 \text{ V}$				100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{GS}} = V_{\text{DS}}, I_D = 20 \mu\text{A}$		2.5		3.5	V
Negative Threshold Temperature Coefficient	$V_{\text{GS}(\text{TH})}/T_J$				-7.6		$\text{mV}/^\circ\text{C}$
Drain-to-Source On Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10 \text{ V}$	$I_D = 10 \text{ A}$		10	12	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{\text{DS}} = 15 \text{ V}, I_D = 10 \text{ A}$			111		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{iss}	$V_{\text{GS}} = 0 \text{ V}, f = 1 \text{ MHz}, V_{\text{DS}} = 25 \text{ V}$		420		pF
Output Capacitance	C_{oss}			230		
Reverse Transfer Capacitance	C_{rss}			11		
Total Gate Charge	$Q_{\text{G}(\text{TOT})}$	$V_{\text{GS}} = 10 \text{ V}, V_{\text{DS}} = 32 \text{ V}; I_D = 10 \text{ A}$		7.9		nC
Threshold Gate Charge	$Q_{\text{G}(\text{TH})}$			1.6		
Gate-to-Source Charge	Q_{GS}			2.5		
Gate-to-Drain Charge	Q_{GD}			1.5		
Plateau Voltage	V_{GP}			4.7		V

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{\text{d}(\text{ON})}$	$V_{\text{GS}} = 10 \text{ V}, V_{\text{DS}} = 32 \text{ V}, I_D = 10 \text{ A}, R_{\text{G}} = 1 \Omega$		8.0		ns
Rise Time	t_r			16		
Turn-Off Delay Time	$t_{\text{d}(\text{OFF})}$			16		
Fall Time	t_f			5.0		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{\text{GS}} = 0 \text{ V}, I_S = 10 \text{ A}$	$T_J = 25^\circ\text{C}$		0.84	1.2	V
			$T_J = 125^\circ\text{C}$		0.71		
Reverse Recovery Time	t_{RR}	$V_{\text{GS}} = 0 \text{ V}, dI_S/dt = 100 \text{ A}/\mu\text{s}, I_S = 10 \text{ A}$			19		ns
Charge Time	t_a				9.0		
Discharge Time	t_b				10		
Reverse Recovery Charge	Q_{RR}				6.7		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

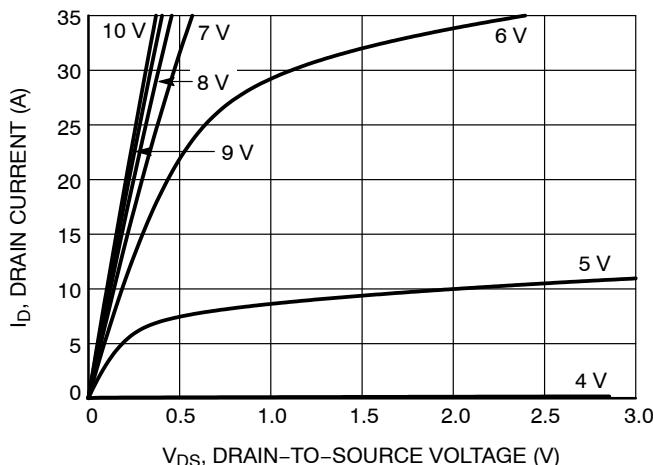


Figure 1. On-Region Characteristics

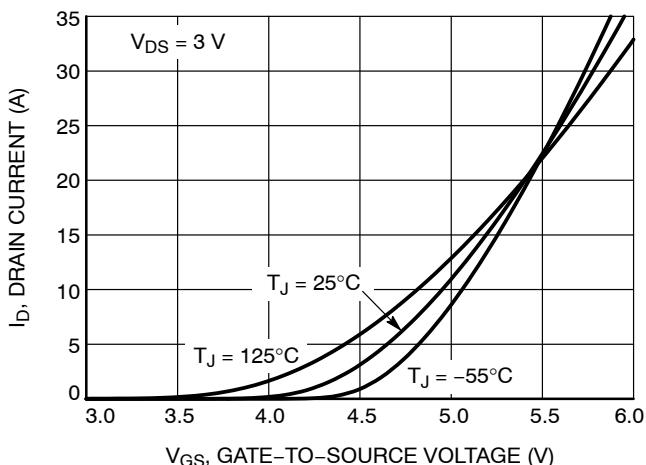


Figure 2. Transfer Characteristics

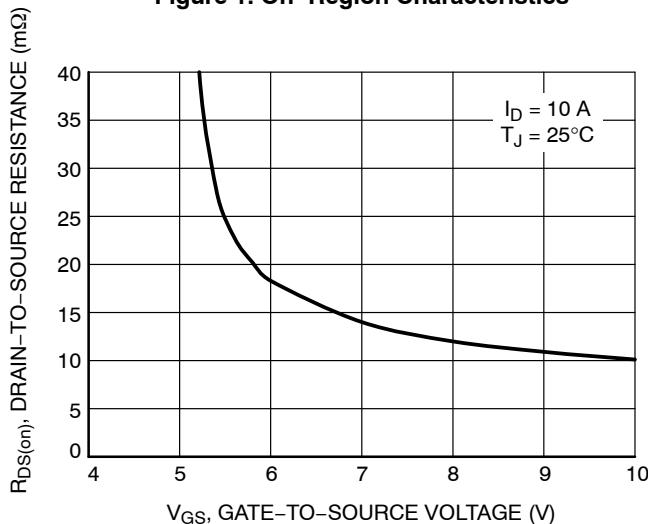


Figure 3. On-Resistance vs. Gate-to-Source Voltage

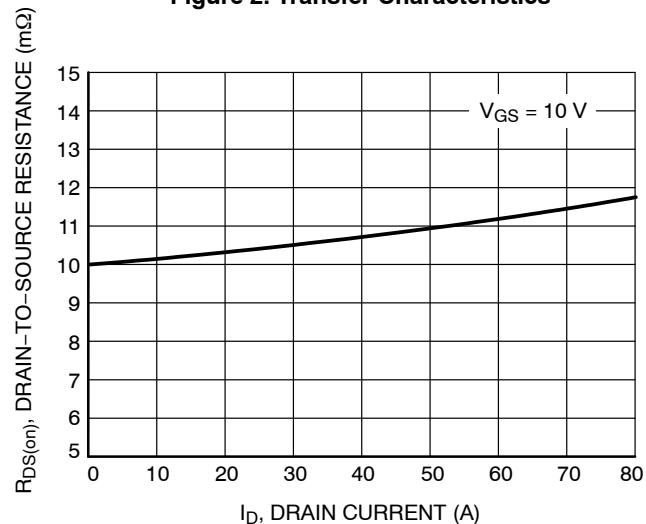


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

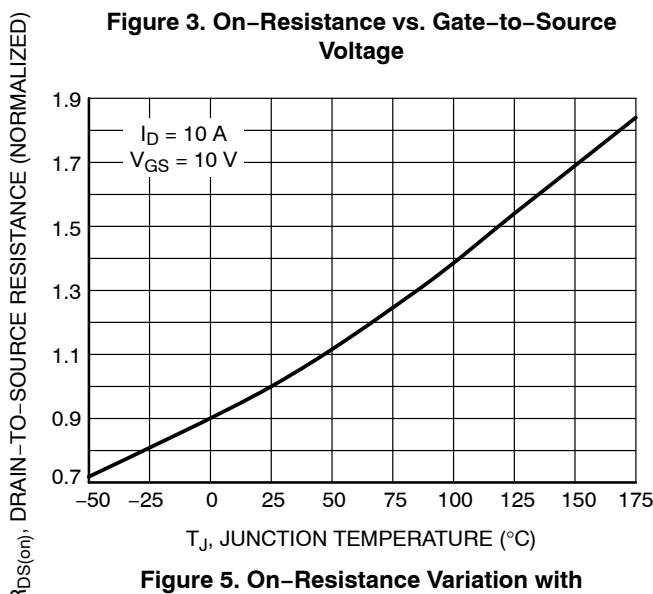


Figure 5. On-Resistance Variation with Temperature

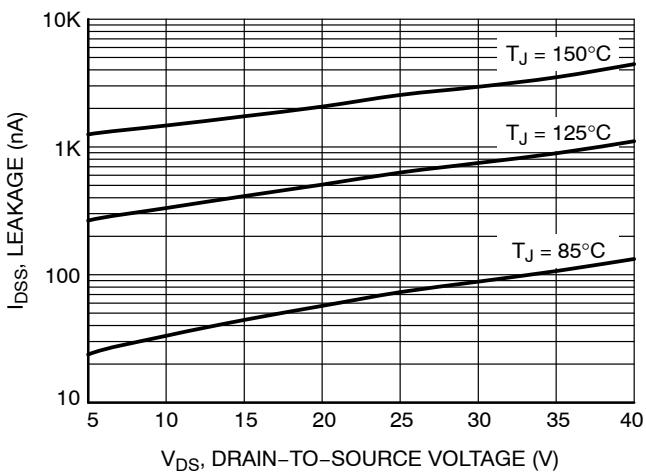
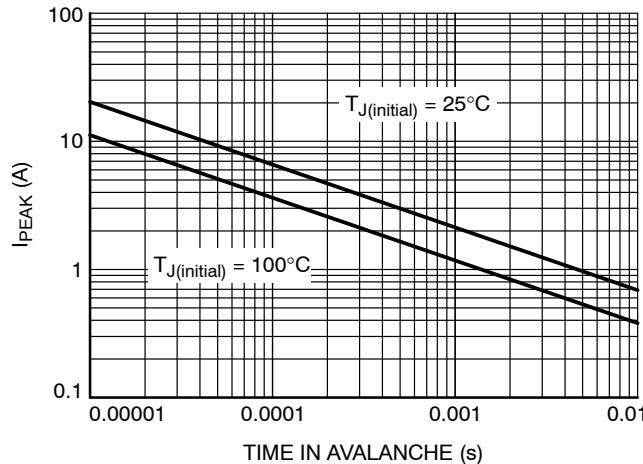
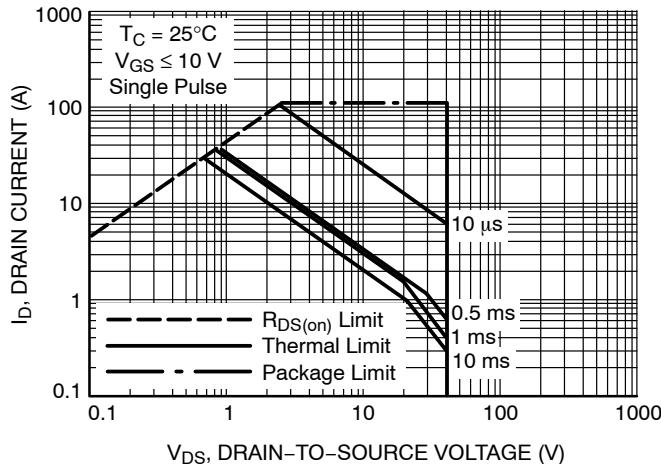
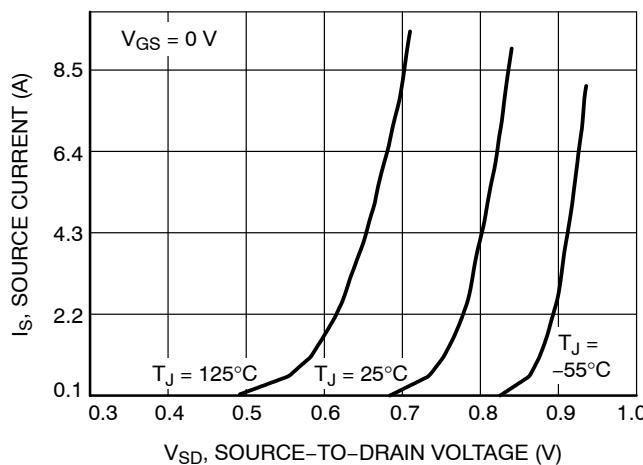
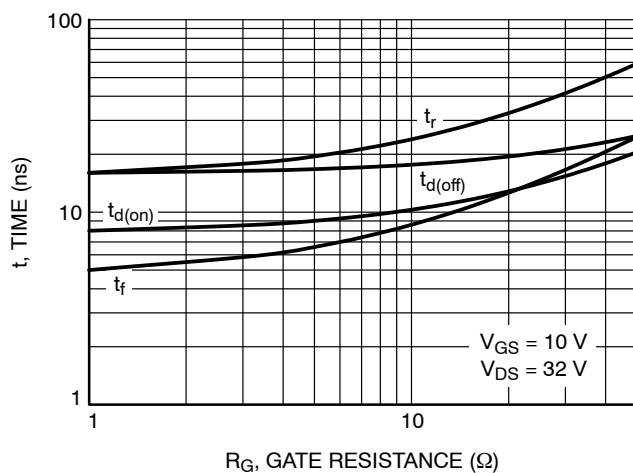
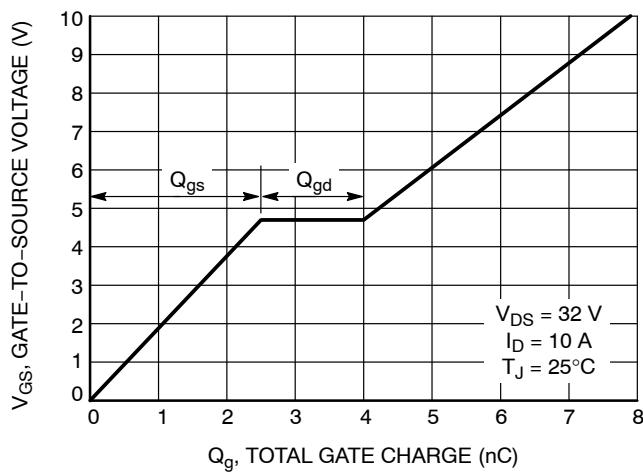
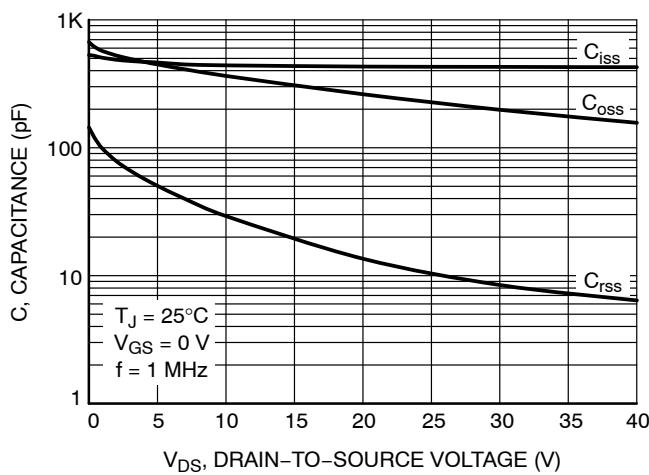


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

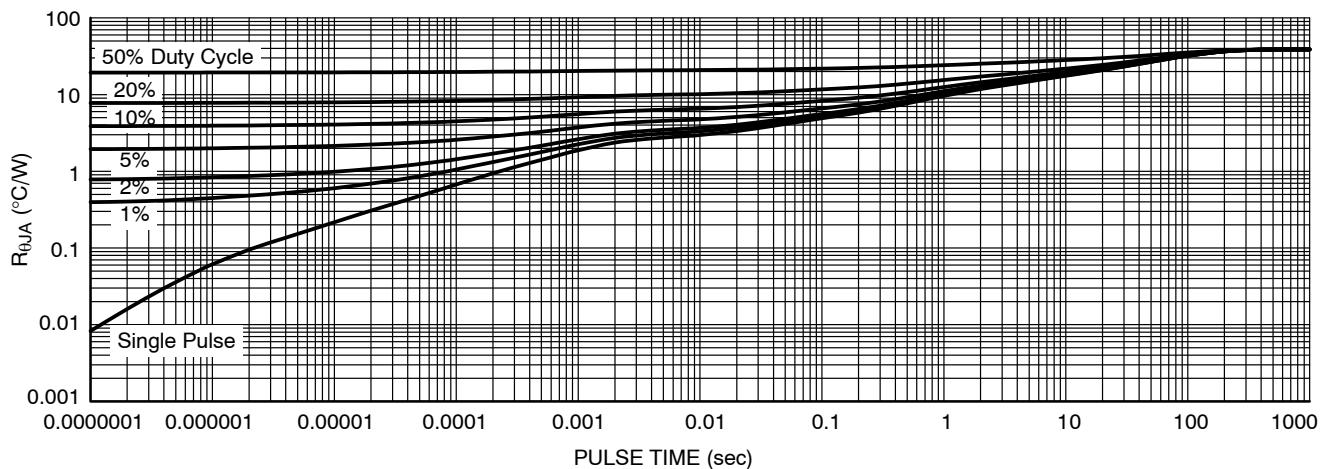


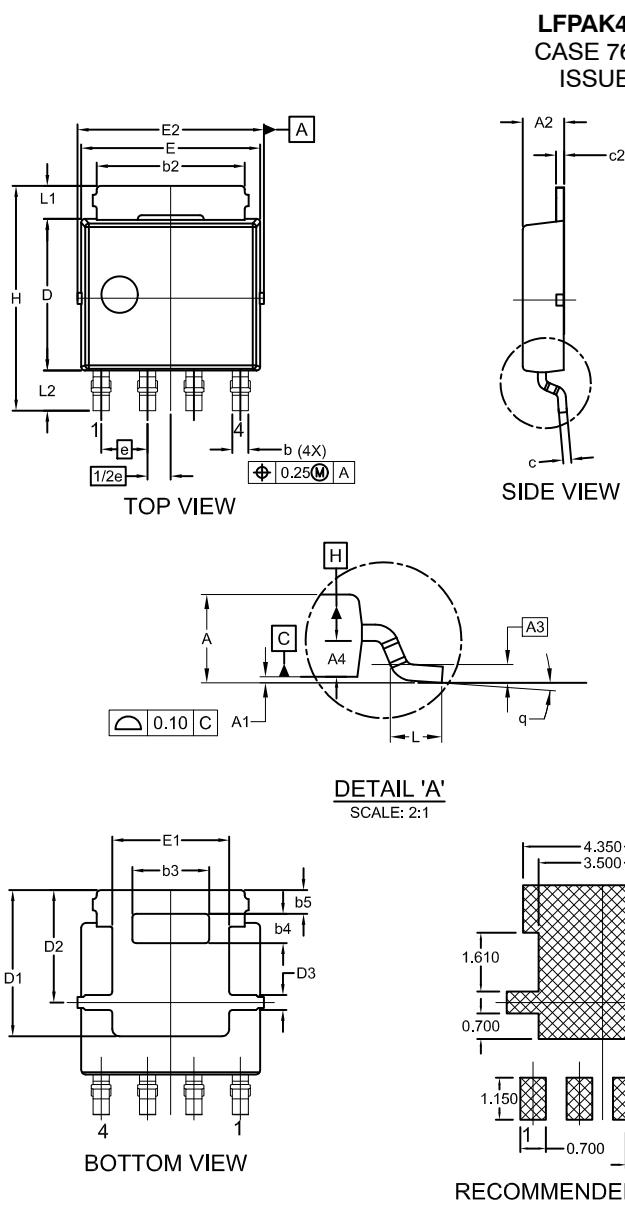
Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NVMYS011N04CTWG	011N04C	LFPAK4 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS



LFPK4 5x6
CASE 760AB
ISSUE B

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.150mm PER SIDE.
4. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

UNIT IN MILLIMETER			
DIM	MIN	NOM	MAX
A	1.10	1.20	1.30
A1	0.00	0.08	0.15
A2	1.10	1.15	1.20
A3	0.25		
A4	0.45	0.50	0.55
b	0.40	0.45	0.50
b2	3.80	4.10	4.40
b3	2.00	2.10	2.20
b4	0.70	0.80	0.90
b5	0.55	0.65	0.75
c	0.19	0.22	0.25
c2	0.19	0.22	0.25
D	4.05	4.15	4.25
D1	3.80	4.00	4.20
D2	3.00	3.10	3.20
D3	0.30	0.40	0.50
E	4.80	4.90	5.00
E1	3.10	3.20	3.30
E2	5.00	5.15	5.30
e	1.27	BSC	
H	6.00	6.15	6.30
L	0.40	0.65	0.85
L1	0.80	0.90	1.00
L2	0.80	1.05	1.30
q	0°	4°	8°

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